

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Priority Application Serial No. .... 09/444,024  
 Priority Filing Date ..... November 19, 1999  
 Inventor ..... Jigish D. Trivedi et al.  
 Assignee ..... Micron Technology, Inc.  
 Priority Group Art Unit ..... 2811  
 Priority Examiner ..... Douglas W. Owens  
 Attorney's Docket No. .... MI22-1965  
 Title: Integrated Circuitry

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 Miller  
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PRELIMINARY AMENDMENT

To: Box Patent Application  
 Assistant Commissioner for Patents  
 Washington, D.C. 20231

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AMENDMENTS

In the Specification

At p. 1 before the "Technical Field" section, please insert the following:

RELATED PATENT DATA

This application resulted from a continuation application of U.S. Patent Application Serial No. 09/444,024, filed November 19, 1999, entitled "P-Type FET in a CMOS With Nitrogen Atoms in the Gate Dielectric", naming Jigish D. Trivedi, Zhongze Wang and Rhongsheng Yang as inventors, which was a divisional application of Patent Application Serial No. 09/386,076, filed August 30, 1999, now Patent No. 6,093,661, issued July 25, 2000, entitled "Integrated Circuitry and

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